

## FEATURES

Complementary Type The NPN Transistor  
MMBT3904 is Recommended  
Epitaxial Planar Die Construction



## MARKING: 2A

## MAXIMUM RATINGS ( $T_a=25$ unless otherwise noted)

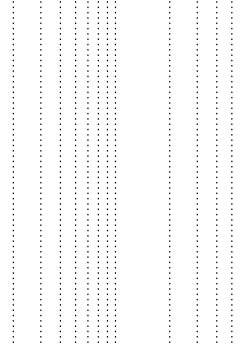
Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-40	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-200	mA
$P_C$	Total Device Dissipation	200	mW
$R_{JA}$	Thermal Resistance Junction to Ambient	625	/W
$T_J$	Junction Temperature	150	
$T_{stg}$	Storage Temperature	-55 ~ +150	

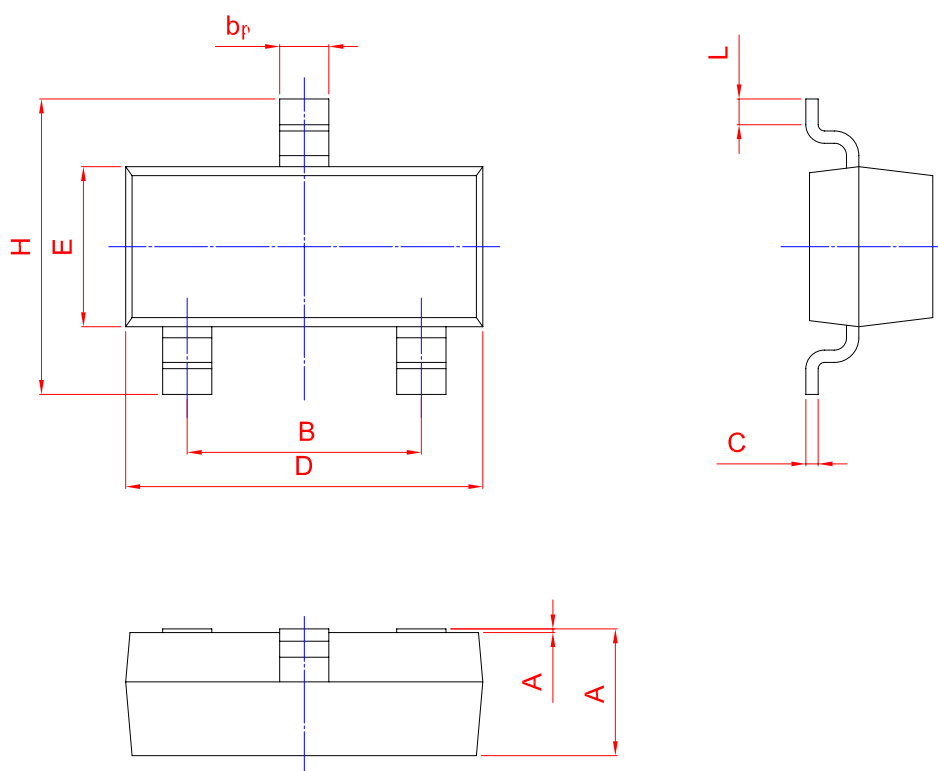
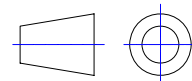
## ELECTRICAL CHARACTERISTICS ( $T_a=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-40		V

## Typical Characteristics

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UNIT	A		$b_p$	C	D	E	$H_E$	$A_1$	$L_p$
mm	1.40		0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95		0.35	0.08	2.70	1.20	2.20	0.013	0.20